

## **Description**

The DMP2070U-13 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

### **General Features**

 $V_{DS} = -20V I_D = -4.1A$   $R_{DS(ON)} < 45 m\Omega @ V_{GS} = -4.5V$ 

ESD Rating: 1500V HBM

## **Application**

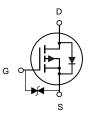
Battery protection

Load switch

Uninterruptible power supply



SOT-23-3L



P-Channel MOSFET

## **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
DMP2070U-13	SOT-23-3L	AFTV	3000

## Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
V <sub>DS</sub>	Drain-Source Voltage	-20	V
Vgs	Gate-Source Voltage	±10	V
I <sub>D</sub>	Drain Current-Continuous	-4.1	A
Ірм	Drain Current-Pulsed (Note 1)	-30	А
P <sub>D</sub>	Maximum Power Dissipation	1.4	W
Тյ,Тѕтс	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	89.3	°C/W



## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

•		,				
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±10V,V <sub>DS</sub> =0V	-	-	±10	μΑ
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250μA	-0.35	-0.55	-0.9	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4A	-	34	45	mΩ
Drain-Source On-State Resistance		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-4A	-	44	60	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =-5V,I <sub>D</sub> =-4A	8	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =-10V,V <sub>GS</sub> =0V, F=1.0MHz	-	950	-	PF
Output Capacitance	Coss		-	165	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F-1.UIVITZ	-	120	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	$V_{DD}$ =-10V,R <sub>L</sub> =2. 5 $\Omega$ $V_{GS}$ =-4.5V,R <sub>GEN</sub> =3 $\Omega$	-	12		nS
Turn-on Rise Time	t <sub>r</sub>		-	10		nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	19		nS
Turn-Off Fall Time	t <sub>f</sub>		-	25		nS
Total Gate Charge	Qg	V <sub>DS</sub> =-10V,I <sub>D</sub> =-4A, V <sub>GS</sub> =-4.5V	-	12		nC
Gate-Source Charge	$Q_{gs}$		-	1.4	-	nC
Gate-Drain Charge	$Q_{gd}$	v GS4.5 v	-	3.6	1	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-4A	-	-	-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-4	Α
		•		•	•	•

#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- **3.** Pulse Test: Pulse Width ≤  $300\mu$ s, Duty Cycle ≤ 2%.
- **4.** Guaranteed by design, not subject to production



## **Typical Electrical And Thermal Characteristics**

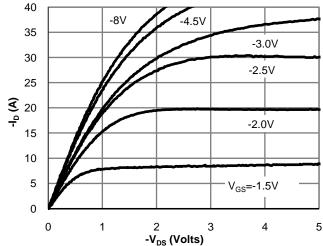


Fig 1: On-Region Characteristics (Note E)

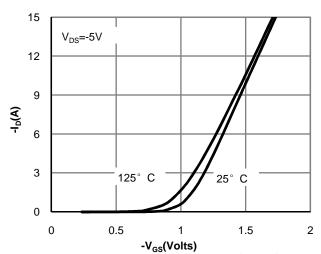


Figure 2: Transfer Characteristics (Note E)

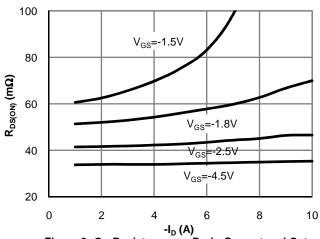


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

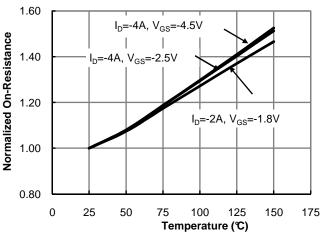


Figure 4: On-Resistance vs. Junction Temperature (Note E)

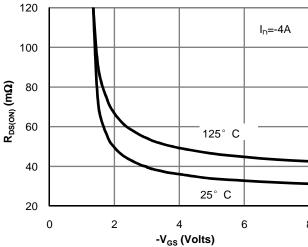


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

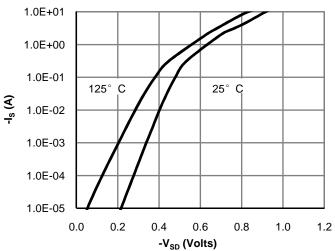
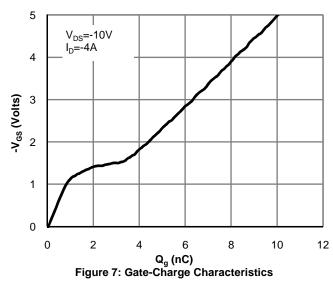
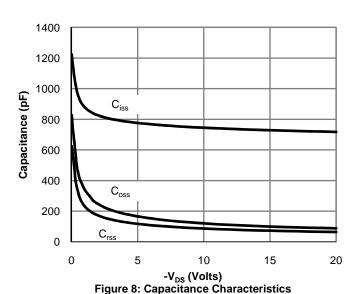
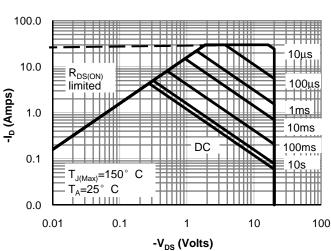


Figure 6: Body-Diode Characteristics (Note E)









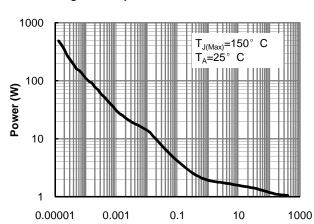


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

Pulse Width (s)
Figure 10: Single Pulse Power Rating Junction-toAmbient (Note F)

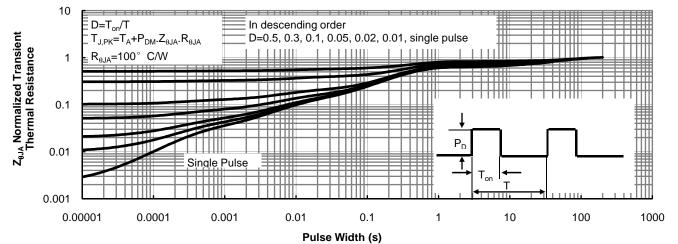
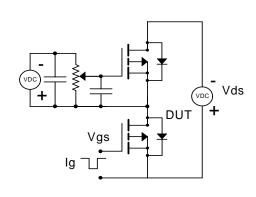
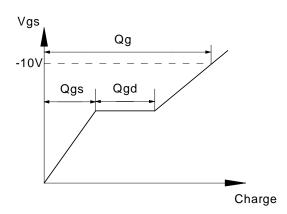


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

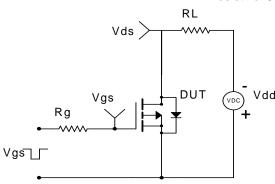


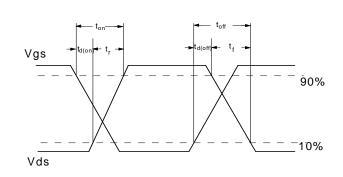
### Gate Charge Test Circuit & Waveform



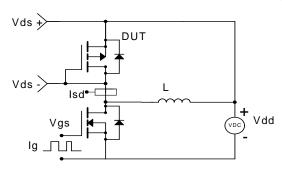


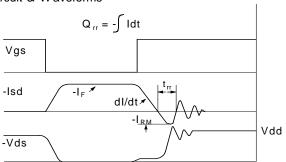
Resistive Switching Test Circuit & Waveforms



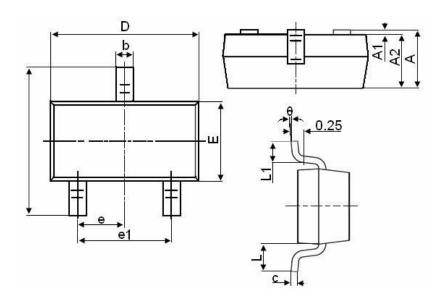


### Diode Recovery Test Circuit & Waveforms





# **SOT-23-3L Package Information**



Symbol	Dimensions in Millimeters			
	MIN.	MAX.		
А	1.050	1.250		
A1	0.000	0.100		
A2	1.050	1.150		
b	0.300	0.500		
С	0.100	0.200		
D	2.800	3.000		
E	1.500	1.700		
E1	2.650	2.950		
е		0.950TYP		
e1	1.800	2.000		
L		0.550REF		
L1	0.300	0.600		
θ	0°	8°		



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